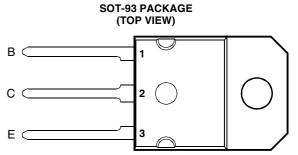
# TIP2955 PNP SILICON POWER TRANSISTOR

# BOURNS®

- Designed for Complementary Use with the TIP3055 Series
- 90 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

#### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Collector-base voltage ( $I_E = 0$ )	V <sub>CBO</sub>	-100	V
Collector-emitter voltage $(I_B = 0)$ (see Note 1)	V <sub>CER</sub>	-70	V
Emitter-base voltage	VEBO	-7	V
Continuous collector current	I <sub>C</sub>	-15	А
Continuous base current	IB	-7	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	Ptot	90	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)	P <sub>tot</sub>	3.5	W
Unclamped inductive load energy (see Note 4)	1/2LIC <sup>2</sup>	62.5	mJ
Operating junction temperature range	Т <sub>ј</sub>	-65 to +150	°C
Storage temperature range	T <sub>stg</sub>	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds	TL	260	°C

NOTES: 1. This value applies when the base-emitter resistance  $R_{BE} = 100 \Omega$ .

- 2. Derate linearly to 150°C case temperature at the rate of 0.72 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH,  $I_{B(on)}$  = -0.4 A,  $R_{BE}$  = 100  $\Omega$ ,  $V_{BE(off)}$  = 0,  $R_S$  = 0.1  $\Omega$ ,  $V_{CC}$  = -10 V.

### PRODUCT INFORMATION

# TIP2955 PNP SILICON POWER TRANSISTOR



#### electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	ТҮР	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> = -30 mA	I <sub>B</sub> = 0	(see Note 5)	-60			V
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> = -30 V	I <sub>B</sub> = 0				-0.7	mA
I <sub>CEV</sub>	Voltage between base and emitter	V <sub>CE</sub> = -100 V	V <sub>BE</sub> = 1.5 V				-5	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> = -7 V	I <sub>C</sub> = 0				-5	mA
h <sub>FE</sub>	Forward current transfer ratio	$V_{CE} = -4 V$ $V_{CE} = -4 V$	$I_{\rm C} = -4A$ $I_{\rm C} = -10 A$	(see Notes 5 and 6)	20 5		70	
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>B</sub> = -0.4 A I <sub>B</sub> = -3.3 A	$I_{\rm C} = -4A$ $I_{\rm C} = -10 A$	(see Notes 5 and 6)			-1.1 -3	V
V <sub>BE</sub>	Base-emitter voltage	V <sub>CE</sub> = -4 V	I <sub>C</sub> = -4 A	(see Notes 5 and 6)			-1.8	V
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = -10 V	I <sub>C</sub> = -0.5 A	f = 1 kHz	20			
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = -10 V	I <sub>C</sub> = -0.5 A	f = 1 MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques,  $t_p = 300 \ \mu s$ , duty cycle  $\leq 2\%$ .

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

#### thermal characteristics

PARAMETER	MIN	ТҮР	MAX	UNIT
R <sub>0JC</sub> Junction to case thermal resistance			1.39	°C/W
R <sub>0JA</sub> Junction to free air thermal resistance			35.7	°C/W

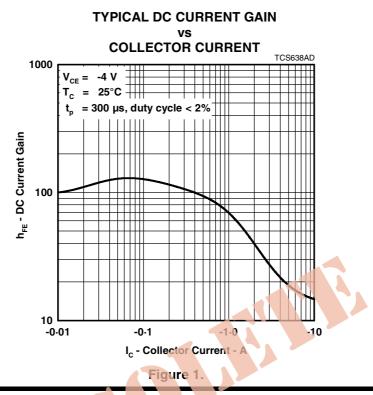
# resistive-load-switching characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS <sup>†</sup>		MIN	ТҮР	MAX	UNIT
t <sub>on</sub> Turn-on time	$I_{\rm C} = -6  {\rm A}$	I <sub>B(on)</sub> = -0.6 A	$I_{B(off)} = 0.6 A$		0.4		μs
t <sub>off</sub> Turn-off time	$V_{BE(off)} = 4 V$	$R_L = 5 \Omega$	$t_p = 20 \ \mu s, \ dc \le 2\%$		0.7		μs

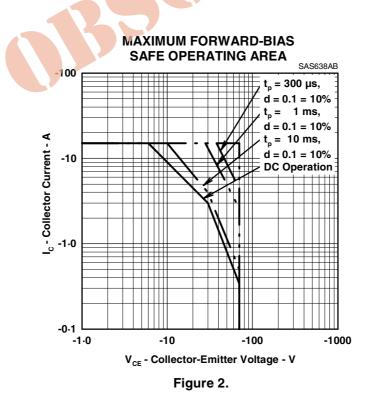
<sup>†</sup> Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



### **TYPICAL CHARACTERISTICS**





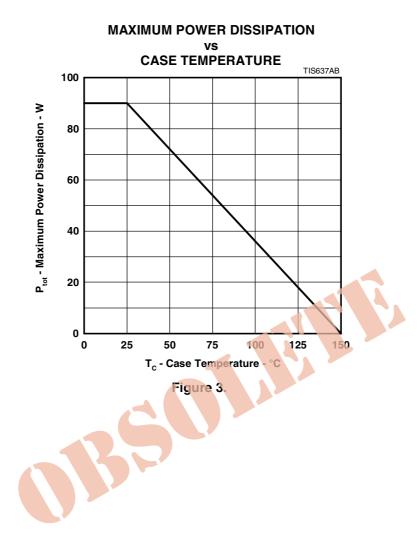


#### PRODUCT INFORMATION

JANUARY 1972 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.



### THERMAL INFORMATION





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